

2N5401

Preferred Device

Amplifier Transistors

PNP Silicon

Features

- Pb-Free Packages are Available*

MAXIMUM RATINGS

| Rating | Symbol | 2N5400 | 2N5401 | Unit |
|---|----------------|-------------|--------|-------------------------------|
| Collector – Emitter Voltage | V_{CEO} | 120 | 150 | Vdc |
| Collector – Base Voltage | V_{CBO} | 130 | 160 | Vdc |
| Emitter – Base Voltage | V_{EBO} | 5.0 | | Vdc |
| Collector Current – Continuous | I_C | 600 | | mAdc |
| Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D | 625 5.0 | | mW mW/ $^\circ\text{C}$ |
| Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C | P_D | 1.5 12 | | Watts mW/ $^\circ\text{C}$ |
| Operating and Storage Junction Temperature Range | T_J, T_{stg} | –55 to +150 | | $^\circ\text{C}$ |

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

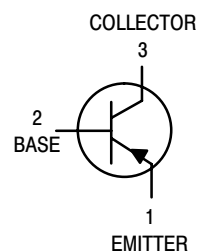
THERMAL CHARACTERISTICS

| Characteristic | Symbol | Max | Unit |
|--|-----------------|------|---------------------------|
| Thermal Resistance, Junction-to-Ambient | $R_{\theta JA}$ | 200 | $^\circ\text{C}/\text{W}$ |
| Thermal Resistance, Junction-to-Case | $R_{\theta JC}$ | 83.3 | $^\circ\text{C}/\text{W}$ |

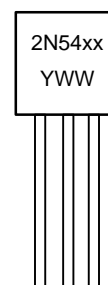


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MARKING DIAGRAM



Y = Year
WW = Work Week

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

Preferred devices are recommended choices for future use and best overall value.

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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|--|---------------|--------|----------|------|
| OFF CHARACTERISTICS | | | | |
| Collector–Emitter Breakdown Voltage ⁽¹⁾ ($I_C = 1.0\text{ mA}$, $I_B = 0$) | $V_{(BR)CEO}$ | 150 | – | Vdc |
| Collector–Base Breakdown Voltage ($I_C = 100\text{ }\mu\text{A}$, $I_E = 0$) | $V_{(BR)CBO}$ | 160 | – | Vdc |
| Emitter–Base Breakdown Voltage ($I_E = 10\text{ }\mu\text{A}$, $I_C = 0$) | $V_{(BR)EBO}$ | 5.0 | – | Vdc |
| Collector Cutoff Current ($V_{CB} = 120\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 120\text{ Vdc}$, $I_E = 0$, $T_A = 100^\circ\text{C}$) | I_{CBO} | – – | 50 50 | |
| Emitter Cutoff Current ($V_{EB} = 3.0\text{ Vdc}$, $I_C = 0$) | I_{EBO} | – | 50 | nAdc |

ON CHARACTERISTICS (Note 1)

| | | | | |
|--|---------------|----------------|---------------|-----|
| DC Current Gain ($I_C = 1.0\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$) ($I_C = 10\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$) ($I_C = 50\text{ mA}$, $V_{CE} = 5.0\text{ Vdc}$) | h_{FE} | 50 60 50 | – 240 – | – |
| Collector–Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 1.0\text{ mA}$) ($I_C = 50\text{ mA}$, $I_B = 5.0\text{ mA}$) | $V_{CE(sat)}$ | – – | 0.2 0.5 | Vdc |
| Base–Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 1.0\text{ mA}$) ($I_C = 50\text{ mA}$, $I_B = 5.0\text{ mA}$) | $V_{BE(sat)}$ | – – | 1.0 1.0 | Vdc |

SMALL–SIGNAL CHARACTERISTICS

| | | | | |
|--|-----------|-----|-----|-----|
| Current–Gain — Bandwidth Product ($I_C = 10\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f = 100\text{ MHz}$) | f_T | 100 | 300 | MHz |
| Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$) | C_{obo} | – | 6.0 | pF |
| Small–Signal Current Gain ($I_C = 1.0\text{ mA}$, $V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$) | h_{fe} | 40 | 200 | – |
| Noise Figure ($I_C = 250\text{ }\mu\text{A}$, $V_{CE} = 5.0\text{ Vdc}$, $R_S = 1.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$) | NF | – | 8.0 | dB |

1. Pulse Test: Pulse Width $\leq 300\text{ }\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

ORDERING INFORMATION

| Device | Package | Shipping [†] |
|-------------|--------------------|-----------------------|
| 2N5401 | TO–92 | 5000 Unit / Bulk |
| 2N5401RL1 | TO–92 | 2000 Tape & Reel |
| 2N5401RLRA | TO–92 | 2000 Tape & Reel |
| 2N5401RLRAG | TO–92 (Pb–Free) | 2000 Tape & Reel |
| 2N5401RLRM | TO–92 | 2000 Tape & Ammo Box |
| 2N5401ZL1 | TO–92 | 2000 Tape & Ammo Box |

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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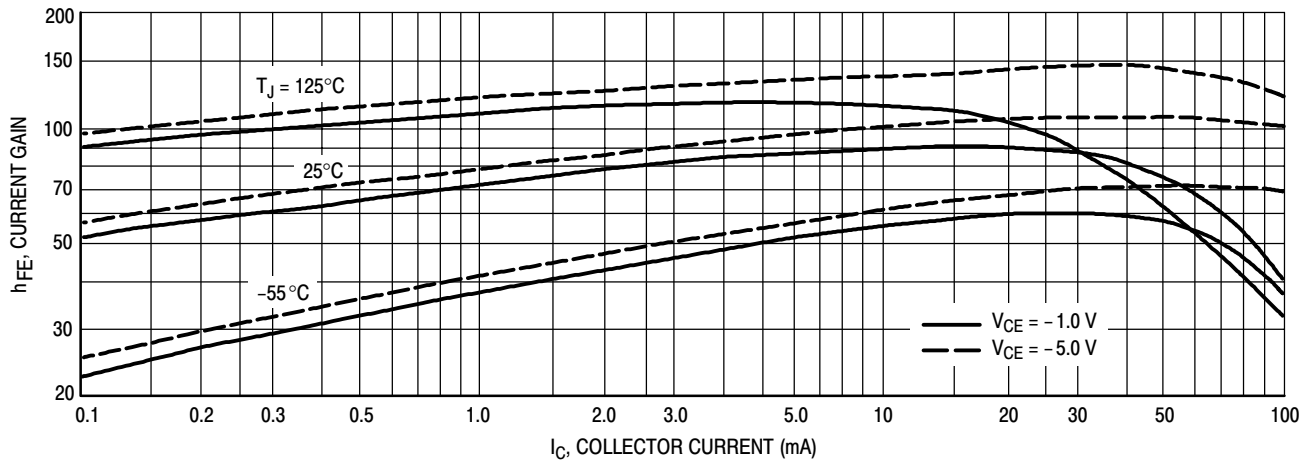


Figure 1. DC Current Gain

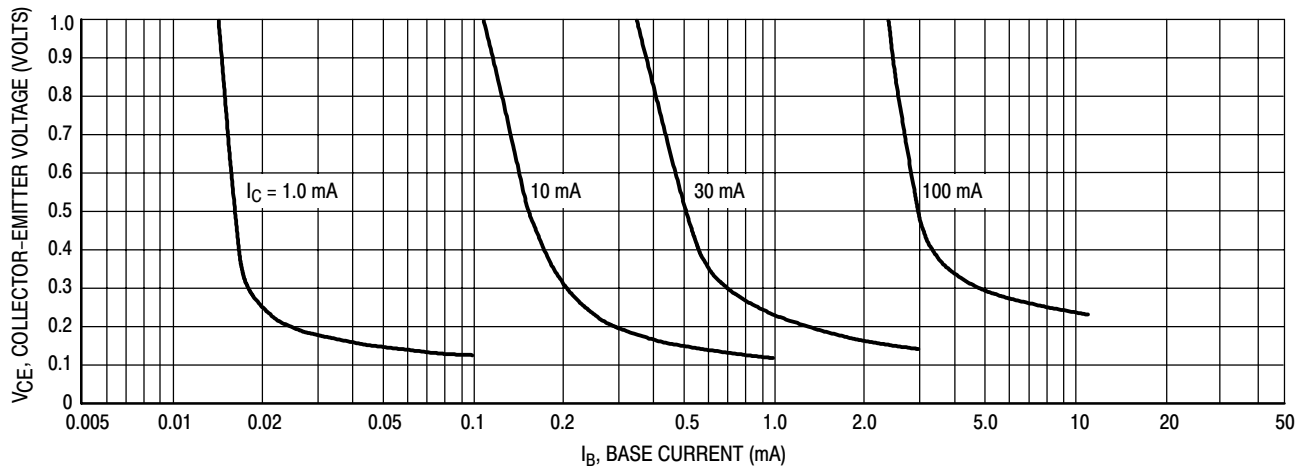


Figure 2. Collector Saturation Region

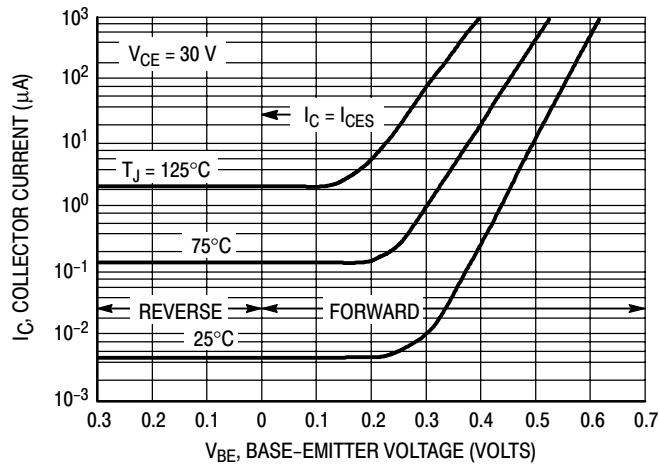


Figure 3. Collector Cut-Off Region

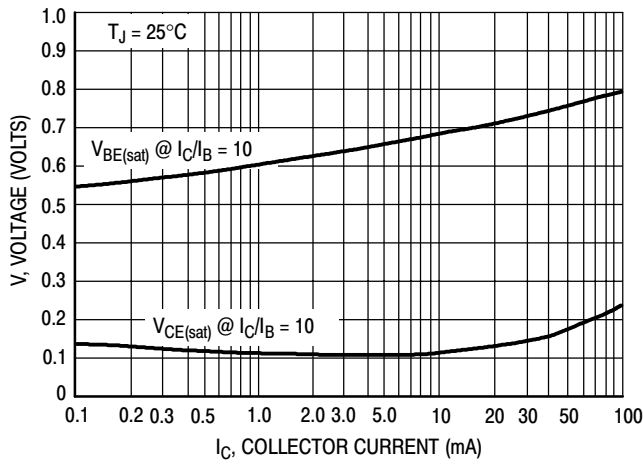


Figure 4. "On" Voltages

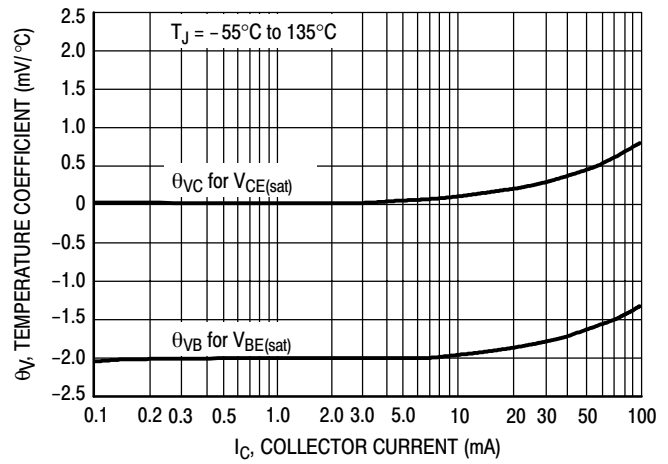


Figure 5. Temperature Coefficients

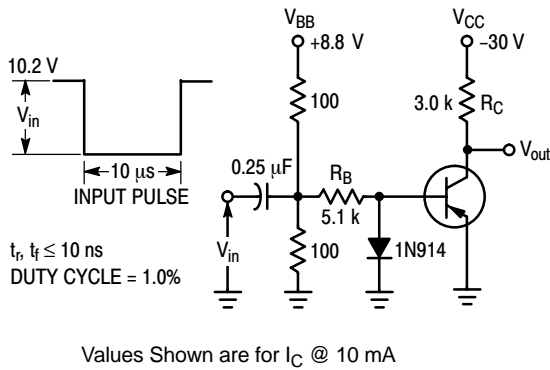


Figure 6. Switching Time Test Circuit

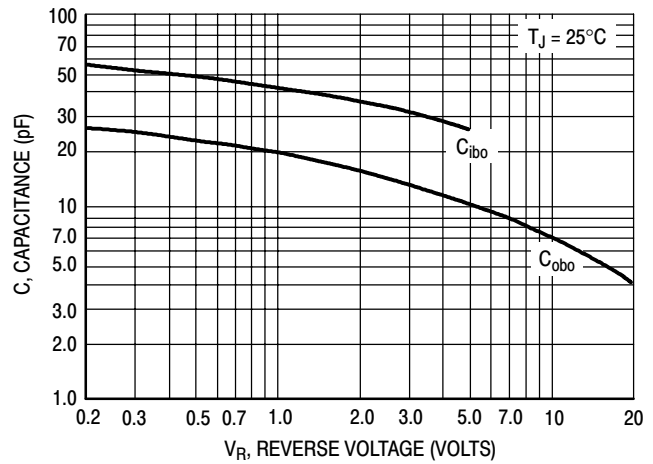


Figure 7. Capacitances

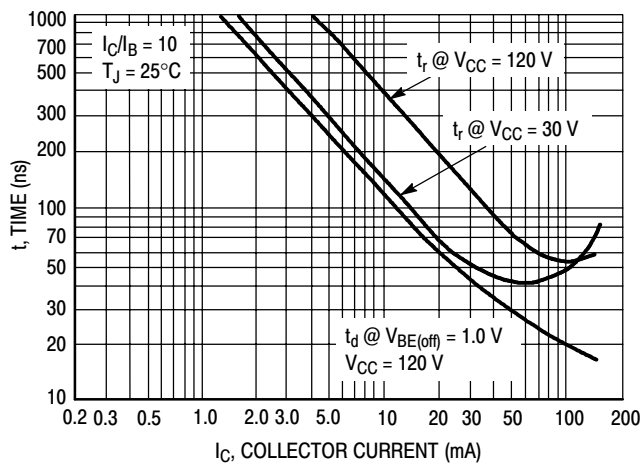


Figure 8. Turn-On Time

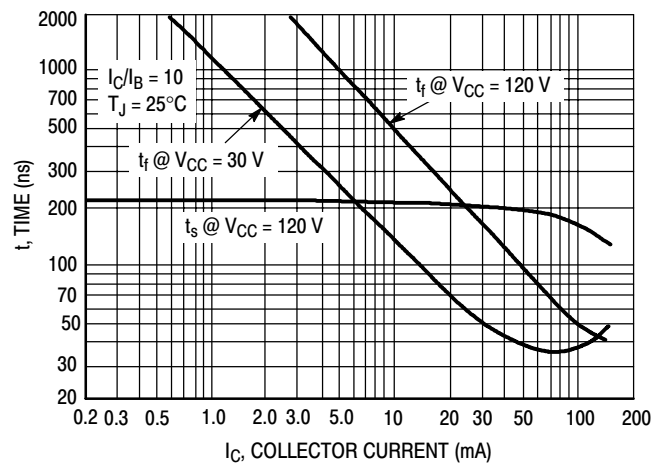
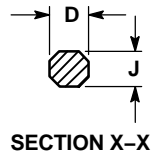
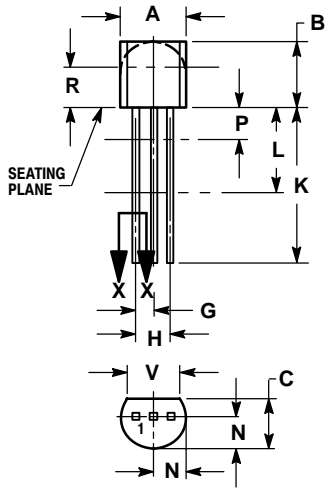


Figure 9. Turn-Off Time

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PACKAGE DIMENSIONS

TO-92
CASE 29-11
ISSUE AL




NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.175 | 0.205 | 4.45 | 5.20 |
| B | 0.170 | 0.210 | 4.32 | 5.33 |
| C | 0.125 | 0.165 | 3.18 | 4.19 |
| D | 0.016 | 0.021 | 0.407 | 0.533 |
| G | 0.045 | 0.055 | 1.15 | 1.39 |
| H | 0.095 | 0.105 | 2.42 | 2.66 |
| J | 0.015 | 0.020 | 0.39 | 0.50 |
| K | 0.500 | --- | 12.70 | --- |
| L | 0.250 | --- | 6.35 | --- |
| N | 0.080 | 0.105 | 2.04 | 2.66 |
| P | --- | 0.100 | --- | 2.54 |
| R | 0.115 | --- | 2.93 | --- |
| V | 0.135 | --- | 3.43 | --- |

STYLE 1:

- PIN 1. EMITTER
- BASE
- COLLECTOR

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